# The RF Line UHF Power Transistor

... designed primarily for wideband, large-signal output and driver amplifier stages to 1.0 GHz.

- Designed for Class A Linear Power Amplifiers
- Specified 25 Volt, 900 MHz Characteristics: Output Power — 3.0 Watts Power Gain — 7.5 dB Min, Class AB
- Gold Metallization for Improved Reliability

# CASE 244-04, STYLE 1

(.280 SOE)

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	VCBO	60	Vdc
Emitter–Base Voltage	VEBO	4.0	Vdc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	29 0.167	Watts W/°C
Operating Junction Temperature	ТJ	200	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

### THERMAL CHARACTERISTICS

[	Characteristic	Symbol	Мах	Unit
ſ	Thermal Resistance, Junction to Case ( $T_C = 70^{\circ}C$ )	R <sub>θ</sub> JC	6.0	°C/W

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•
Collector–Emitter Breakdown Voltage ( $I_C = 15 \text{ mA}, I_B = 0$ )	V(BR)CEO	30	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_{C} = 15 \text{ mA}, V_{BE} = 0)$	V <sub>(BR)</sub> CES	60	-	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 15 \text{ mA}, I_E = 0$ )	V <sub>(BR)</sub> CBO	60	-	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = 5.0 \text{ mA}, I_C = 0)$	V <sub>(BR)EBO</sub>	4.0	-	-	Vdc
Collector Cutoff Current $(V_{CB} = 25 \text{ V}, I_E = 0)$	ICBO	_	-	2.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 500 mA, $V_{CE}$ = 5.0 V)	hFE	20	—	80	—
DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>CB</sub> = 28 V, $I_E$ = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	-	9.8	pF
FUNCTIONAL TESTS			-	-	
Common–Emitter Amplifier Power Gain (V <sub>CE</sub> = 25 V, P <sub>out</sub> = 3.0 W, f = 900 MHz, I <sub>C</sub> = 0.4 A)	GPE	7.5	8.5	-	dB
Load Mismatch (V <sub>CE</sub> = 25 V, I <sub>C</sub> = 0.4 A, P <sub>out</sub> = 3.0 W, f = 900 MHz, Load VSWR = $\infty$ :1, All Phase Angles)	Ψ	No Degradation in Output Power			



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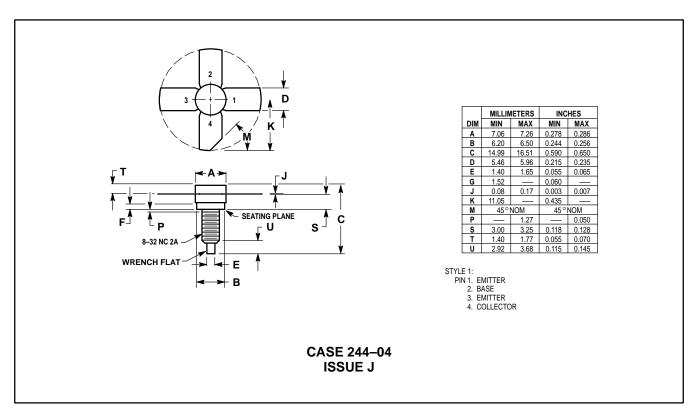




3.0 W, TO 1.0 GHz LINEAR

UHF POWER TRANSISTOR NPN SILICON

### PACKAGE DIMENSIONS



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